-100V P-Channel Enhancement Mode MOSFET

Description

The SX8P10MSI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

V_{DS} = -100V I_D =-8.2A

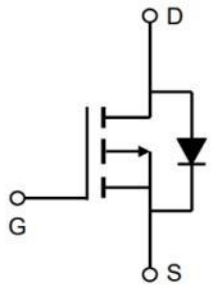
$R_{DS(ON)}$ < 290mΩ @ V_{GS}=-10V

Application

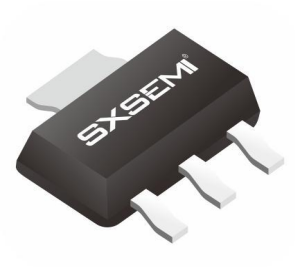
Brushless motor

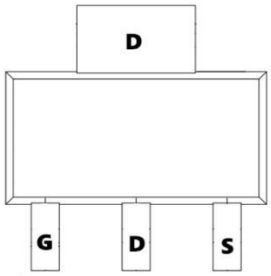
Load switch

Uninterruptible power supply



SOT-223-3L





Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	-8.2	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	-4.5	A
I_{DM}	Pulsed Drain Current[2]	-24.8	A
EAS	Single Pulse Avalanche Energy[3]	58	mJ
P_D@T_C=25℃	Total Power Dissipation[4]	21.3	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	62.5	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	5.4	℃/W

Electrical Characteristics (T_J=25℃, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ	Max.	Units
BVDSS	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = -250μA	-100	117	-	V
IDSS	Zero Gate Voltage Drain Current	V_{DS} = -100V, V_{GS} = 0V	-	-	1	μA
IGSS	Gate to Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
VGS(th)	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = -250μA	-1.2	-1.85	-2.5	V
RDS(on)	Static Drain-Source On-Resistance note1	V_{GS} = -10V, I_D = -5A	-	250	300	mΩ
		V_{GS} = -4.5V, I_D = -3A	-	260	340	
Ciss	Input Capacitance	V_{DS} = -50V, V_{GS} = 0V, f = 1.0MHz	-	760	-	pF
Coss	Output Capacitance		-	25	-	pF
Crss	Reverse Transfer Capacitance		-	12	-	pF
Q_g	Total Gate Charge	V_{DD} = -50V, I_D = -5A, V_{GS} = -10V	-	11.5	-	nC
Q_{gs}	Gate-Source Charge		-	1.3	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	2.9	-	nC
td(on)	Turn-On Delay Time	V_{DS} = -50V, I_D = -5A R_G=4.5Ω, R_L=25Ω V_{GEN} = - 10 V	-	12	-	ns
t_r	Turn-On Rise Time		-	5	-	ns
td(off)	Turn-Off Delay Time		-	35	-	ns
t_f	Turn-Off Fall Time		-	20	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	-12.8	A
VSD	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S =-1A	-	-	-1.3	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0V, I_{sd}= -3A, di/dt =100A/μs	-	25	-	nS
Q_{rr}	Reverse Recovery Charge		-	20	-	nC

Note：

1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width .The EAS data shows Max. rating .

3、The power dissipation is limited by 175℃ junction temperature

4、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

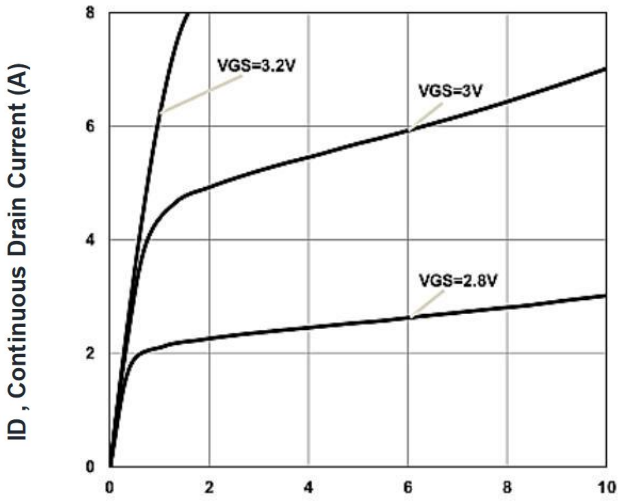


Figure 1. Typical Output Characteristics

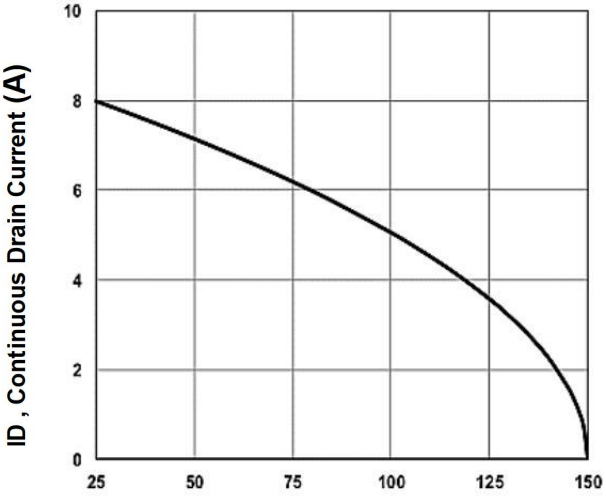


Figure 2. Continuous Drain Current vs. TC

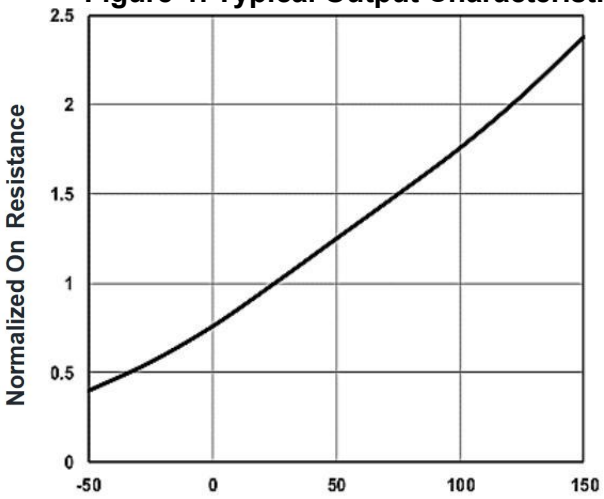


Figure 3.Normalized RDSON vs. TJ

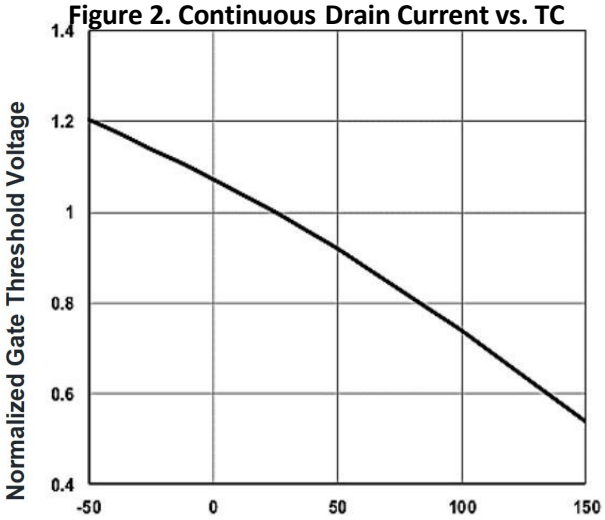


Figure 5.Normalized V th vs. T

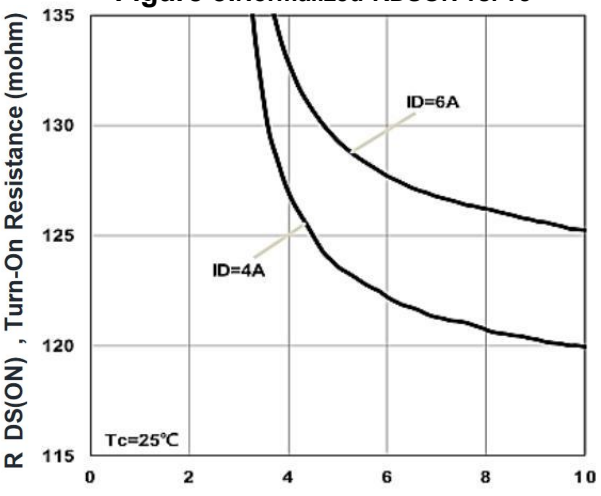


Figure 6. Turn-On Resistance vs. VGS

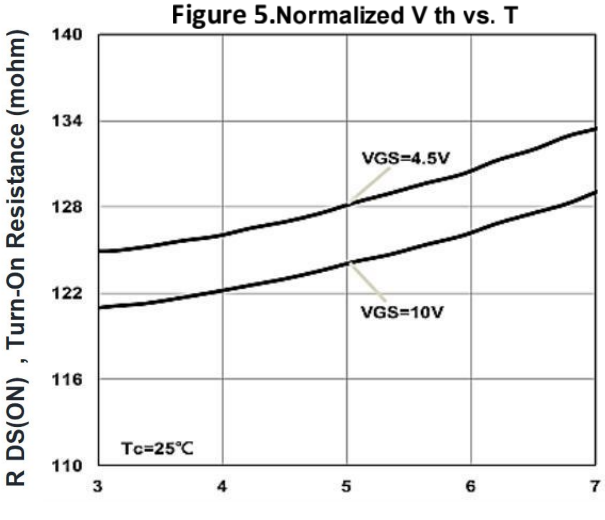


Figure 7.Turn-On Resistance vs. I D

Typical Characteristics

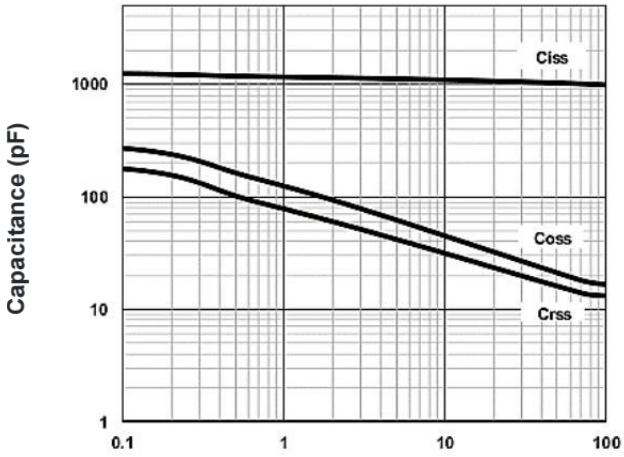


Figure 8. Capacitance Characteristics

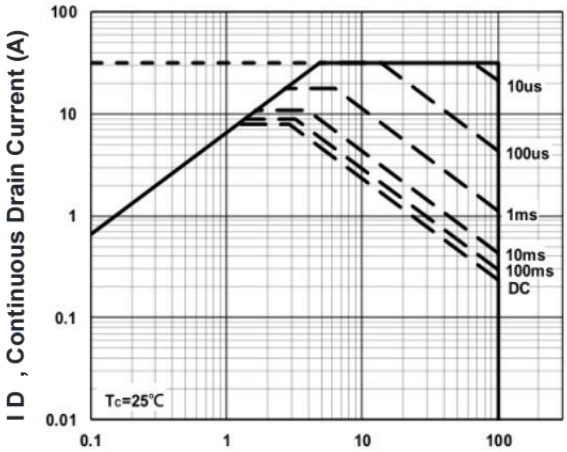


Figure 9. Maximum Safe Operation Area

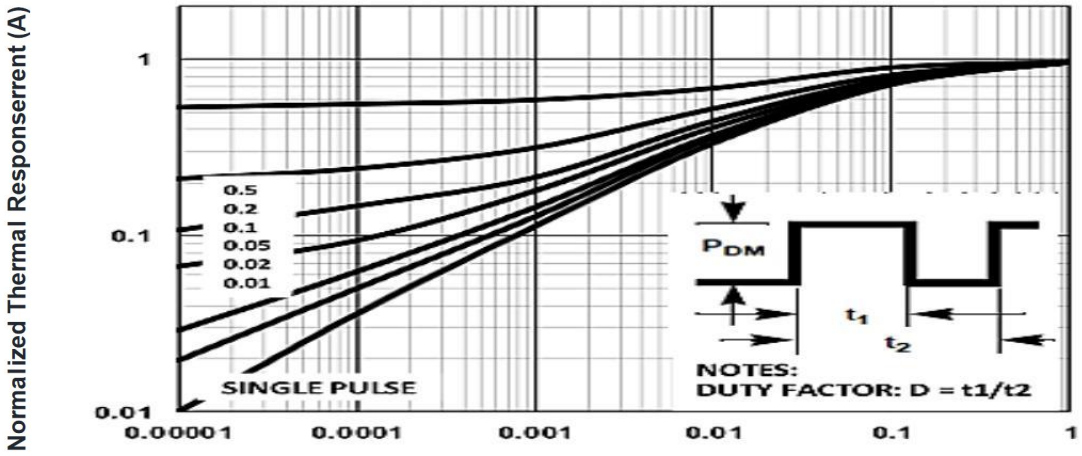


Figure 10. Normalized Transient Impedance

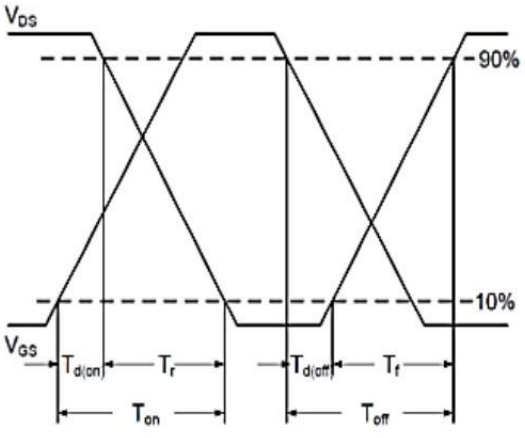


Figure 10. Switching Time Waveform

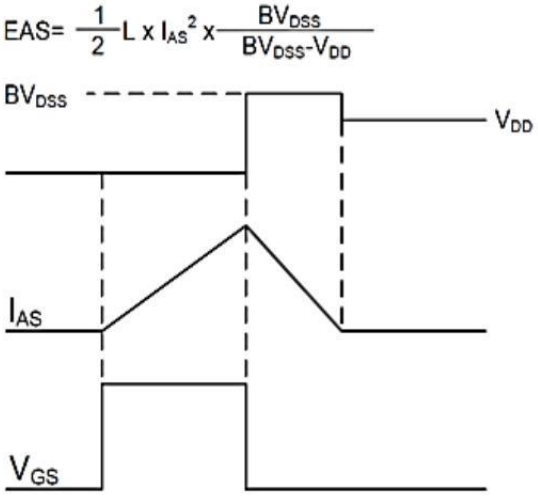
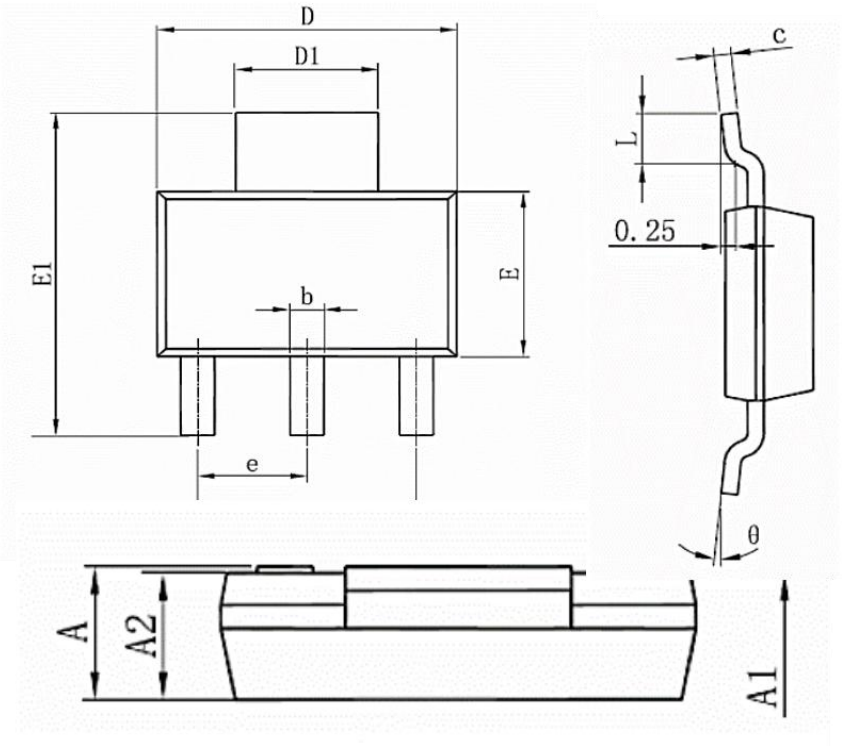


Figure 11. Unclamped Inductive Switching Waveform

Package Mechanical Data:SOT223-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.52	1.8	0.06	0.049
A1	0.000	0.100	0.000	0.004
A2	1.5	1.7	0.059	0.045
b	0.66	0.82	0.026	0.032
c	0.25	0.35	0.010	0.014
D	6.2	6.4	0.244	0.252
D1	2.9	3.1	0.114	0.122
E	3.3	3.7	0.130	0.146
E1	6.83	7.07	0.269	0.278
e	2.300(BSC)		0.037(BSC)	
e1	4.500	4.700	0.177	0.185
L	0.900	1.15	0.035	0.045
θ	0°	10°	0°	10°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOT223-3L		3000